

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	1346	(form or forming or formed) adj3 (oxygen adj3 containing)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/08/26 11:35
2	BRS	L2	18079	(forming or form or forms or formed) adj3 (nitrogen)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/08/26 11:37
3	BRS	L3	30	1 same 2	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/08/26 11:49
4	BRS	L4	8	3 same (hydrogen or H2)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/08/26 11:55
5	BRS	L5	1	(re-oxidize or re-oxydizing or re-oxydized) same (oxygen adj3 containing)	USPAT	2002/08/26 11:55

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L6	1	(re-oxidize or re-oxydizing or re-oxydized) same (oxygen adj3 containing)	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 11:56
7	BRS	L7	8429	(forming or forms or formed) same (oxygen adj3 containing)	USPAT	2002/08/26 12:40
8	BRS	L8	11162	(forming or forms or formed) same (oxygen adj3 containing)	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 12:41
9	BRS	L9	38	8 and (re-oxidizer or re-oxidize or re-oxidized or re-oxidizing)	USPAT; US-PGP; UB; EPO; JPO; DERWENT; IBM_TDB	2002/08/26 13:14
10	BRS	L10	799	(re adj3 (oxidized or orxidize or oxidizing))	USPAT	2002/08/26 13:16
11	BRS	L11	22	10 same (oxygen adj3 (contain or containing or contains))	USPAT	2002/08/26 13:23

CLIPPEDIMAGE= JP02000091577A

PAT-NO: JP02000091577A

DOCUMENT-IDENTIFIER: JP 2000091577 A

TITLE: METHOD OF FORMING GATE OXIDE FILM

PUBN-DATE: March 31, 2000

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APPL-DATE: August 25, 1999

INT-CL (IPC): H01L029/78;H01L021/3065 ;H01L021/316

ABSTRACT:

PROBLEM TO BE SOLVED: To provide a thin and high-quality gate oxide film.

SOLUTION: In this method, formation of an ultrathin gate oxide film 14 of a field-effect transistor 10 is conducted. In this case, the gate oxide film 14 is formed by adjusting the partial pressure of the mixed gas of an oxidizing agent with an etchant so that the oxidizing agent (such as an N<sub>2</sub>O and an CO<sub>2</sub>) is combined with the etchant (such as H<sub>2</sub>) and the thin (to 12

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